

REMARKS

This is intended as a full and complete response to the Office Action dated May 14, 2003, having a shortened statutory period for response set to expire on August 14, 2003. Claims 26-45 have been allowed. Claim 14 has been rewritten in independent form to include the limitations of the base claim and the intervening claims. New claims 46-47 have been added to more clearly recite aspects of the invention. Paragraph [0028] in the specification has been amended to correct a typographical error. Applicants believe no new matter has been introduced by the amendments and the new claims presented herein. The amendments and the new claims have been made in a good faith effort to advance prosecution on the merits. Applicants reserve the right to subsequently take up prosecution of the claims as originally filed in this application in a continuation, a continuation-in-part and/or a divisional application. Please reconsider the claims pending in the application for reasons discussed below.

In a telephone interview on August 12, 2003, Applicants discussed with the Examiner how U.S. Patent No. 6,491,832 ("*Yoshioka*") fails to teach all the limitations of claim 11. The Examiner indicated that he would review *Yoshioka* in light of the position taken by Applicants with respect to claim 11 and claims depending therefrom. Applicants appreciate the Examiner's courtesy for scheduling and conducting the interview.

Claims 11-13 stand rejected under 35 USC 102(e) as being anticipated by U.S. Patent No. 6,491,832 ("*Yoshioka*"). Applicants respectfully traverse this rejection.

Applicants respectfully submit that *Yoshioka* does not teach or disclose flowing HCl as a plasma source material into the plasma reactor. In contrast, *Yoshioka* proposes etching the laminated layer formed on the substrate by using chlorine. More specifically, *Yoshioka* uses a post etch process to remove residual chlorine. This process includes introducing H₂O or methanol into the reactor to react with the residual chlorine and form HCl as a volatile compound for removal from the reactor. *Yoshioka* does not teach or suggest using HCl as the etching gas. Therefore, claim 11 is distinguishable from and patentable over *Yoshioka*. Claims 12 and 13 are also patentable over *Yoshioka* since they depend from claim 11.

Claims 14-15 stand objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Claim 14 has been rewritten in independent form to include all of the limitations of the base claim and the intervening claims. Therefore, claim 14 is in condition for allowance. Claim 15 is also in condition for allowance since it depends from claim 14.

The Examiner has rejected various dependent claims. However, because the rejections to the respective base claims have been overcome, Applicants submit that the rejections for the dependent claims have been obviated.

With regard to new claims 46-47, Applicants submit that claims 46-47 recite subject matter that is neither disclosed, taught, nor otherwise suggested by the cited references, and as such, allowance of these claims is respectfully requested.

In conclusion, the references cited by the Examiner, neither alone nor in combination, teach, show, or suggest the claimed method or apparatus. Having addressed all issues set out in the office action, Applicants respectfully submit that the claims are in condition for allowance and respectfully request that the claims be allowed.

The prior art made of record is noted. However, it is believed that the secondary references are no more pertinent to the Applicants' disclosure than the primary references cited in the office action. Therefore, it is believed that a detailed discussion of the secondary references is not deemed necessary for a full and complete response to this office action. Accordingly, allowance of the claims is respectfully requested.

Respectfully submitted,



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